March 2015

FDD3860

N-Channel PowerTrench® MOSFET

100V, 29A, 36mΩ

Features

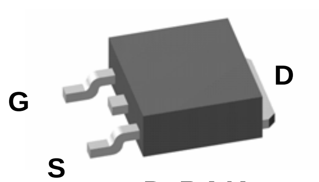
- Max $r_{DS(on)}$ = 36mΩ at V_{GS} = 10V, I_D = 5.9A
- High performance trench technology for extremely low $r_{DS(on)}$
- 100% UIL tested
- RoHS Compliant

General Description

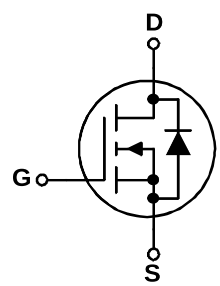
This N-Channel MOSFET is rugged gate version of Fairchild Semiconductor‘s advanced Power Trench® process. This part is tailored for low $r_{DS(on)}$ and low Qg figure of merit, with avalanche ruggedness for a wide range of switching applications.

Applications

- DC-AC Conversion
- Synchronous Rectifier



D-PAK
(TO-252)



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Silicon limited) T_C = 25°C	29	A
	-Continuous T_A = 25°C (Note 1a)	6.2	
	-Pulsed	60	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	121	mJ
P_D	Power Dissipation T_C = 25°C	69	W
	Power Dissipation T_A = 25°C (Note 1a)	3.1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	40	

Package Marking and Ordering Information

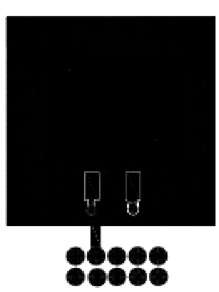
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD3860	FDD3860	D-PAK (TO-252)	13’’	16mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

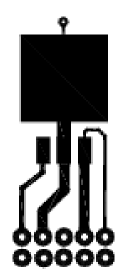
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		98		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 250μA	2.5	3.8	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-11.4		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 5.9A		29	36	mΩ
		V_{GS} = 10V, I_D = 5.9A, T_J = 125°C		51	64	
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 5.9A		20		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz		1310	1740	pF
C_{oss}	Output Capacitance			100	130	pF
C_{rss}	Reverse Transfer Capacitance			45	70	pF
R_g	Gate Resistance	f = 1MHz		1.6		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_D = 5.9A, V_{GS} = 10V, R_{GEN} = 6Ω		16	29	ns
t_r	Rise Time			10	21	ns
$t_{d(off)}$	Turn-Off Delay Time			24	39	ns
t_f	Fall Time			7	15	ns
Q_g	Total Gate Charge at 10V	V_{DD} = 50V, I_D = 5.9A		22	31	nC
Q_{gs}	Gate to Source Charge			7.1		nC
Q_{gd}	Gate to Drain "Miller" Charge			6.3		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 2.0A (Note 2)		0.7	1.2	V
		V_{GS} = 0V, I_S = 5.9A (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	I_F = 5.9A, di/dt = 100A/μs		34	55	ns
Q_{rr}	Reverse Recovery Charge			40	64	nC

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a) 40°C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 96°C/W when mounted on a minimum pad.

2: Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

3: Starting T_J = 25°C, L = 3mH, I_{AS} = 9A, V_{DD} = 100V, V_{GS} = 10V.

Typical Characteristics T_J = 25°C unless otherwise noted

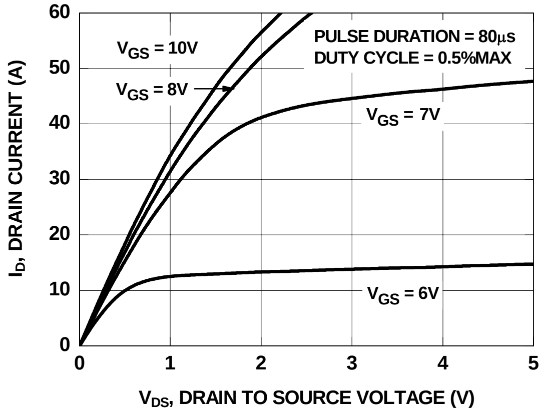


Figure 1. On-Region Characteristics

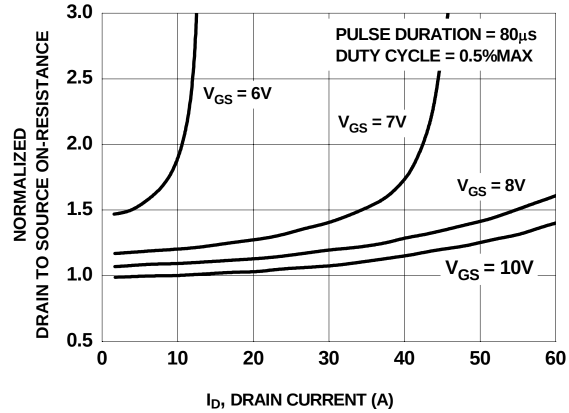


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

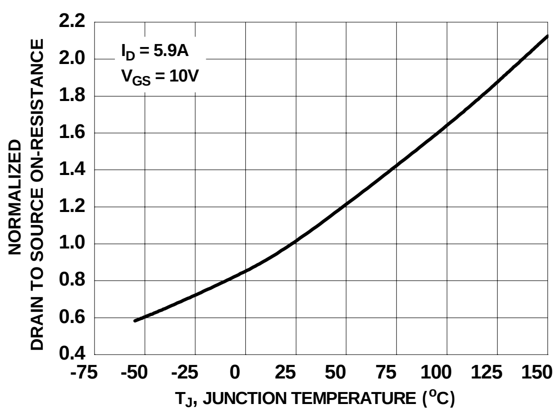


Figure 3. Normalized On-Resistance vs Junction Temperature

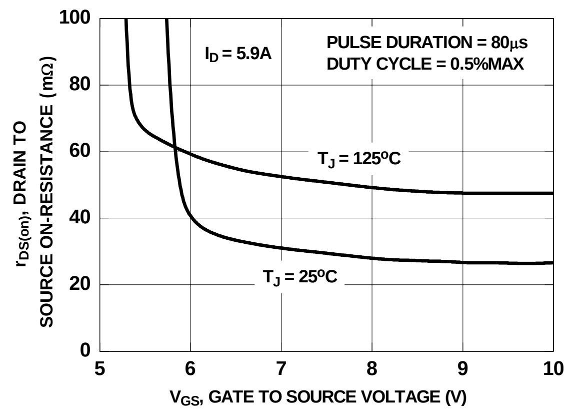


Figure 4. On-Resistance vs Gate to Source Voltage

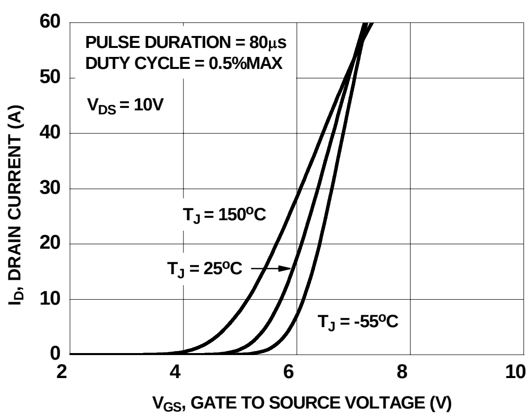


Figure 5. Transfer Characteristics

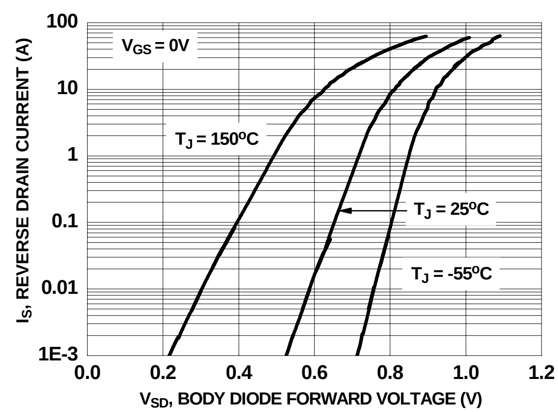


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

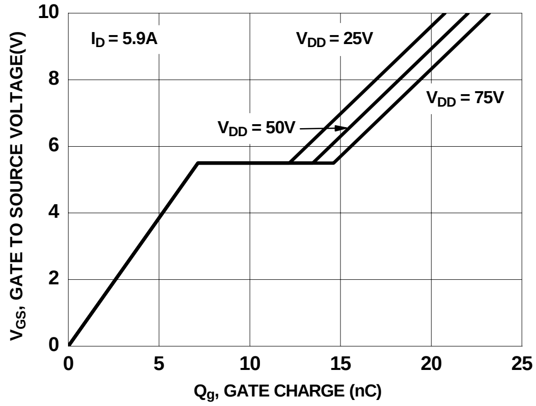


Figure 7. Gate Charge Characteristics

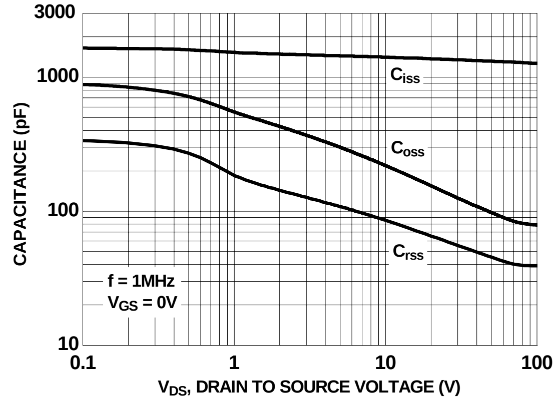


Figure 8. Capacitance vs Drain to Source Voltage

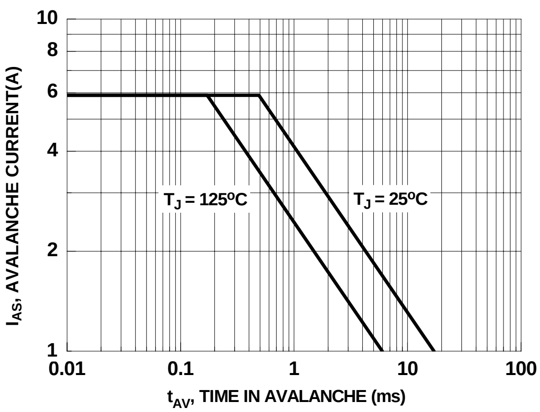


Figure 9. Unclamped Inductive Switching Capability

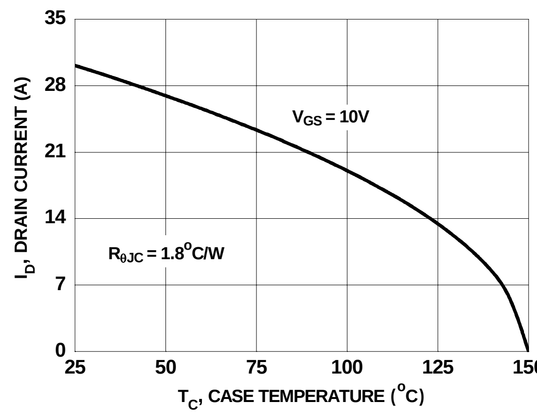


Figure 10. Maximum Continuous Drain Current vs Case Temperature

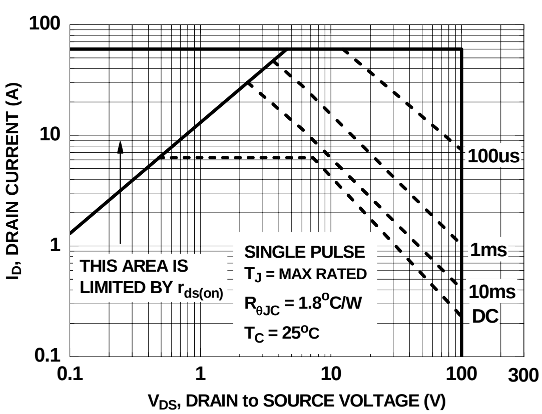


Figure 11. Forward Bias Safe Operating Area

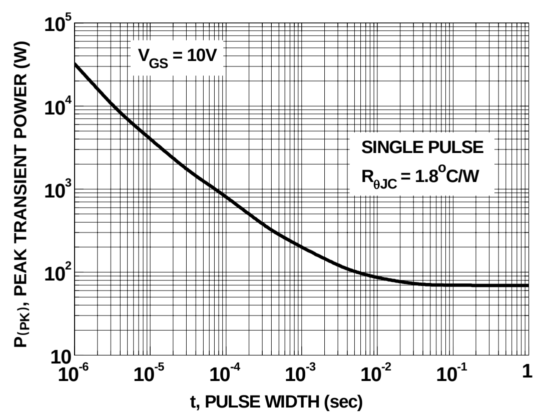


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

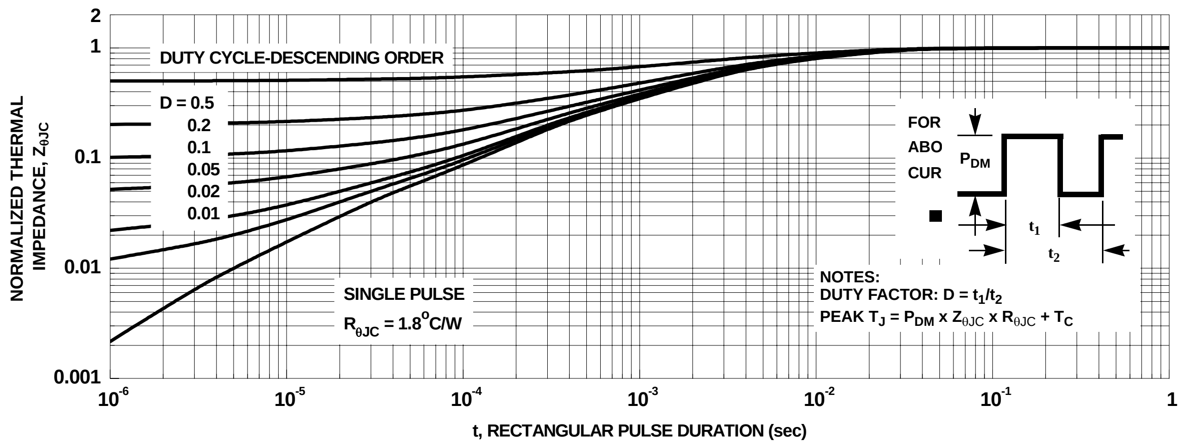


Figure 13. Transient Thermal Response Curve

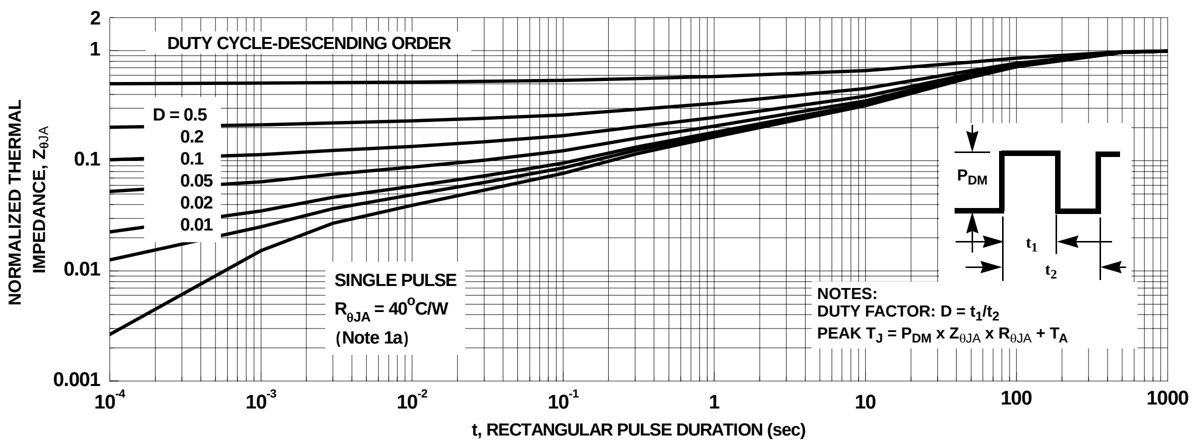


Figure 14. Transient Thermal Response Curve

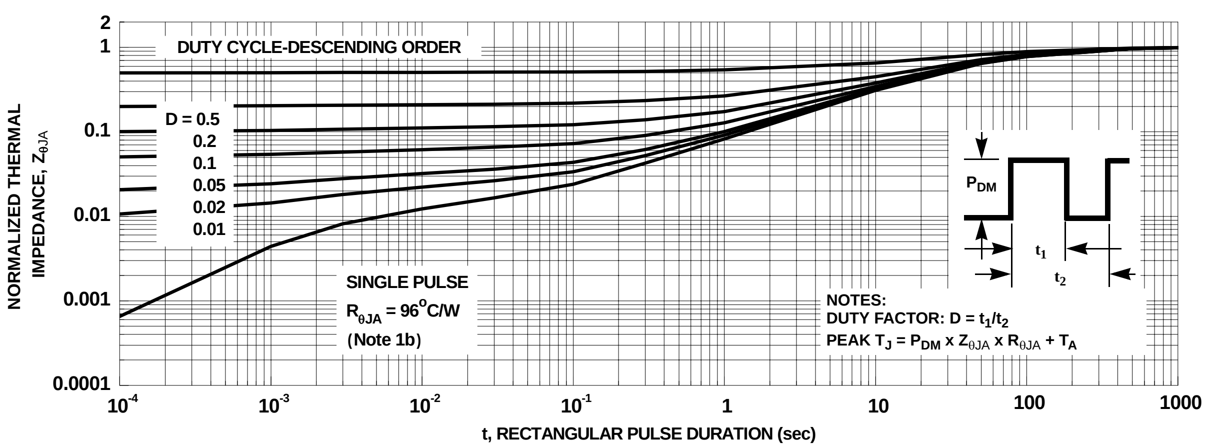
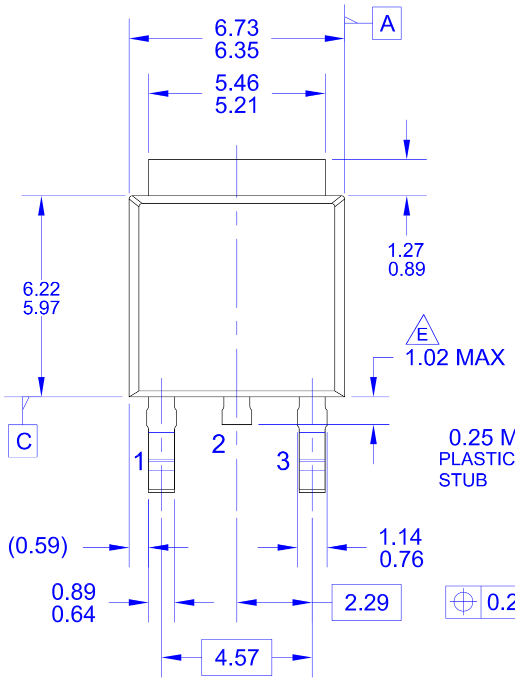
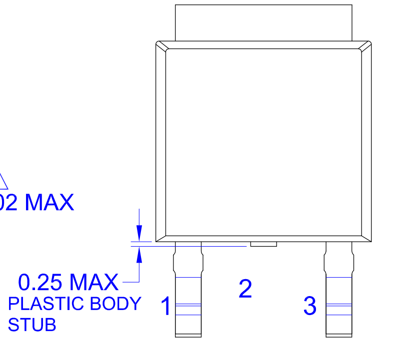


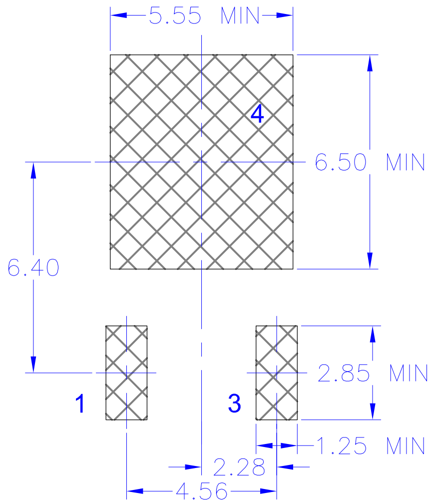
Figure 15. Transient Thermal Response Curve



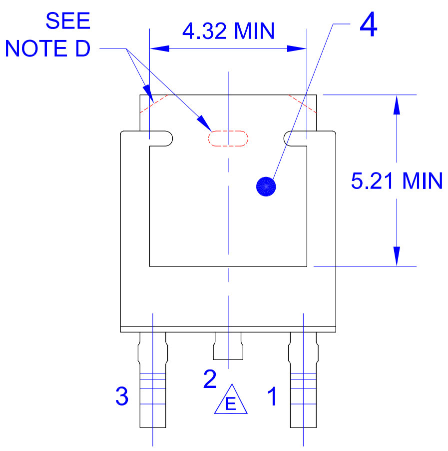
NON-DIODE PRODUCTS VERSION



DIODE PRODUCTS VERSION



LAND PATTERN RECOMMENDATION



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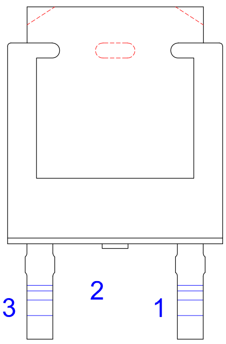

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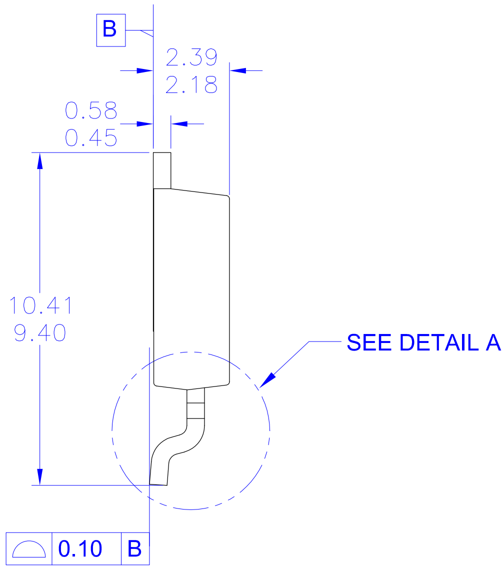


NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

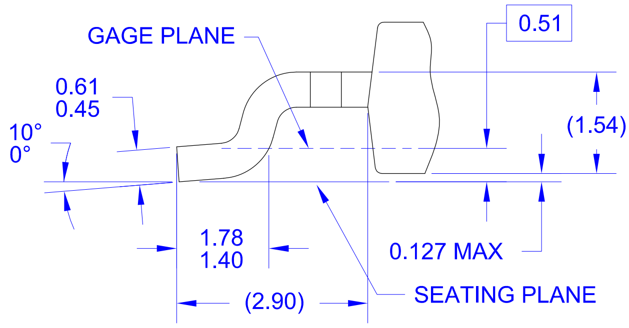
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.

E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS

F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV10



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SCALE: 12X

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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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